

# IGBT - Field Stop II

## NGTB35N65FL2WG

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

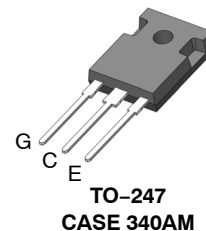
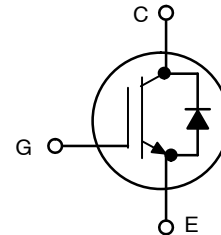
**35 A, 650 V**  
 **$V_{CEsat} = 1.70 V$**   
 **$E_{off} = 0.28 mJ$**

### Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 5  $\mu s$  Short-Circuit Capability
- These are Pb-Free Devices

### Typical Applications

- Solar Inverters
- Uninterruptible Power Supplies (UPS)
- Welding

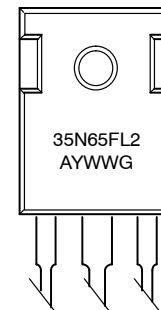


### ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter Voltage	$V_{CES}$	650	V
Collector Current @ $T_C = 25^{\circ}C$ @ $T_C = 100^{\circ}C$	$I_C$	70 35	A
Diode Forward Current @ $T_C = 25^{\circ}C$ @ $T_C = 100^{\circ}C$	$I_F$	70 35	A
Diode Pulsed Current $T_{PULSE}$ Limited by $T_J$ Max	$I_{FM}$	120	A
Pulsed Collector Current, $T_{pulse}$ Limited by $T_{Jmax}$	$I_{CM}$	120	A
Short-circuit Withstand Time $V_{GE} = 15 V, V_{CE} = 400 V,$ $T_J \leq +150^{\circ}C$	$t_{SC}$	5	$\mu s$
Gate-emitter Voltage	$V_{GE}$	$\pm 20$	V
Transient Gate-emitter Voltage ( $T_{PULSE} = 5 \mu s, D < 0.10$ )		$\pm 30$	V
Power Dissipation @ $T_C = 25^{\circ}C$ @ $T_C = 100^{\circ}C$	$P_D$	300 150	W
Operating Junction Temperature Range	$T_J$	-55 to +175	$^{\circ}C$
Storage Temperature Range	$T_{stg}$	-55 to +175	$^{\circ}C$
Lead temperature for soldering, 1/8" from case for 5 seconds	$T_{SLD}$	260	$^{\circ}C$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### MARKING DIAGRAM



35N65FL2 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
NGTB35N65FL2WG	TO-247 (Pb-Free)	30 Units / Rail

# NGTB35N65FL2WG

## THEMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.50	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	1.00	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	650	-	-	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 35\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 35\text{ A}, T_J = 175^{\circ}\text{C}$	$V_{CEsat}$	1.50 -	1.70 2.20	2.00 -	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 350\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}, T_J = 175^{\circ}\text{C}$	$I_{CES}$	-	-	0.5 4.0	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	-	-	200	nA

### DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$	-	3115	-	pF
Output capacitance		$C_{oes}$	-	149	-	
Reverse transfer capacitance		$C_{res}$	-	88	-	
Gate charge total	$V_{CE} = 480\text{ V}, I_C = 35\text{ A}, V_{GE} = 15\text{ V}$	$Q_g$	-	125	-	nC
Gate to emitter charge		$Q_{ge}$	-	30	-	
Gate to collector charge		$Q_{gc}$	-	63	-	

### SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 35\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$	-	72	-	ns	
Rise time		$t_r$	-	40	-		
Turn-off delay time		$t_{d(off)}$	-	132	-		
Fall time			$t_f$	-	75	-	mJ
Turn-on switching loss		$E_{on}$	-	0.84	-		
Turn-off switching loss		$E_{off}$	-	0.28	-		
Total switching loss		$E_{ts}$	-	1.12	-		
Turn-on delay time		$T_J = 150^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 35\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$	-	70	-	ns
Rise time			$t_r$	-	38	-	
Turn-off delay time	$t_{d(off)}$		-	135	-		
Fall time			$t_f$	-	96	-	mJ
Turn-on switching loss	$E_{on}$		-	1.05	-		
Turn-off switching loss	$E_{off}$		-	0.50	-		
Total switching loss	$E_{ts}$		-	1.55	-		

### DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 35\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 35\text{ A}, T_J = 175^{\circ}\text{C}$	$V_F$	1.50 -	2.20 2.25	2.90 -	V
Reverse recovery time	$T_J = 25^{\circ}\text{C}$ $I_F = 35\text{ A}, V_R = 200\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$t_{rr}$	-	68	-	ns
Reverse recovery charge		$Q_{rr}$	-	265	-	nC
Reverse recovery current		$I_{rrm}$	-	7	-	A
Reverse recovery time	$T_J = 175^{\circ}\text{C}$ $I_F = 35\text{ A}, V_R = 400\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$t_{rr}$	-	156	-	ns
Reverse recovery charge		$Q_{rr}$	-	836	-	nC
Reverse recovery current		$I_{rrm}$	-	8.43	-	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NGTB35N65FL2WG

## TYPICAL CHARACTERISTICS

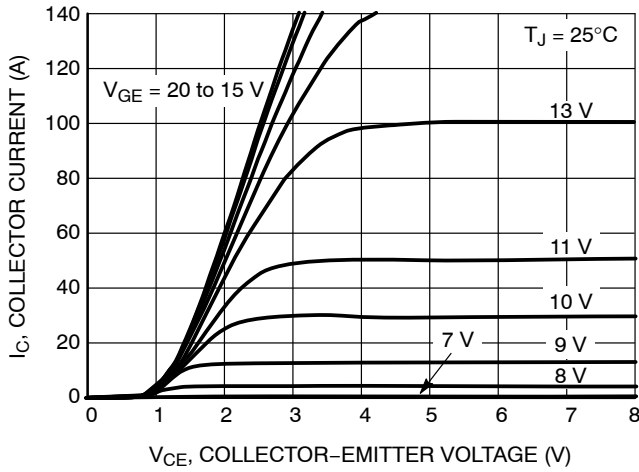


Figure 1. Output Characteristics

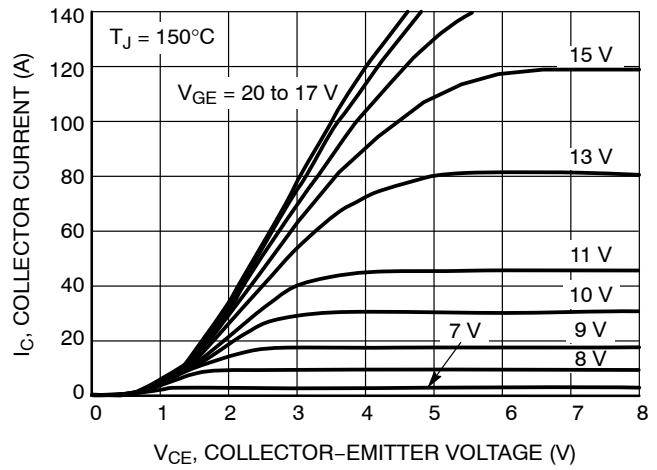


Figure 2. Output Characteristics

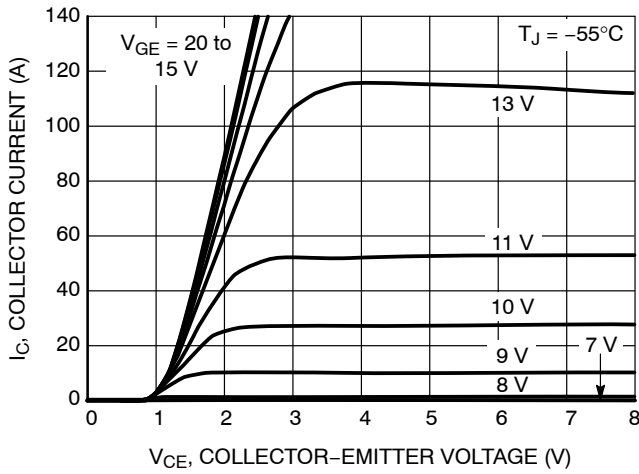


Figure 3. Output Characteristics

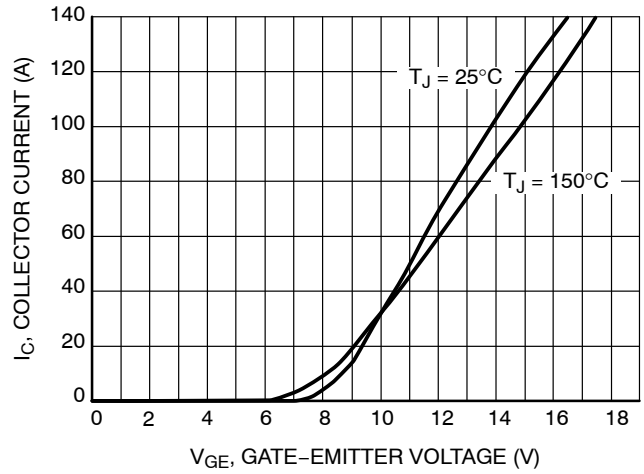


Figure 4. Typical Transfer Characteristics

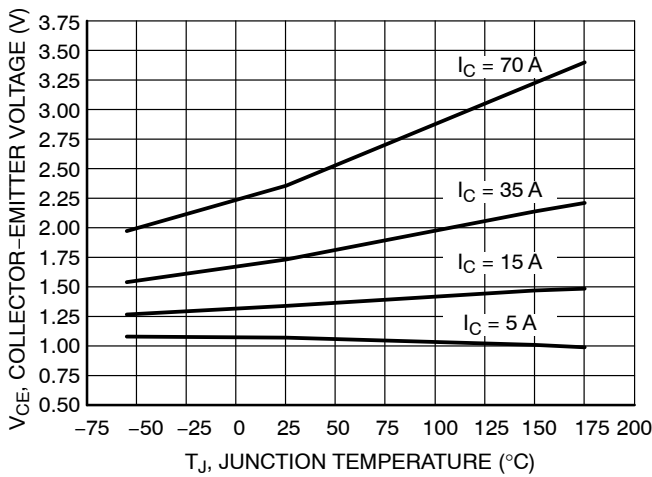


Figure 5.  $V_{CE(sat)}$  vs.  $T_J$

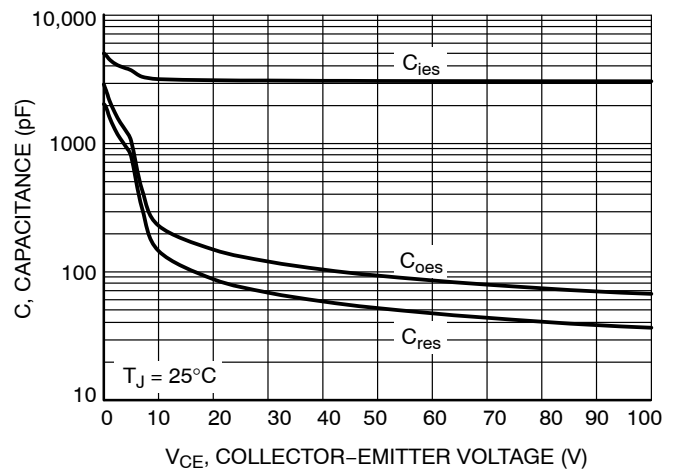


Figure 6. Typical Capacitance

# NGTB35N65FL2WG

## TYPICAL CHARACTERISTICS

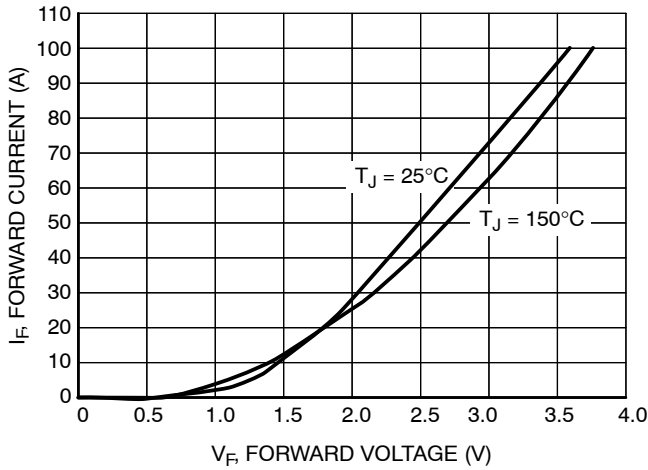


Figure 7. Diode Forward Characteristics

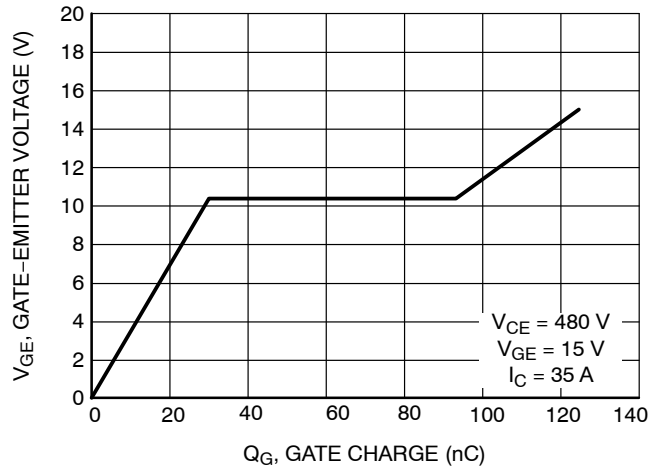


Figure 8. Typical Gate Charge

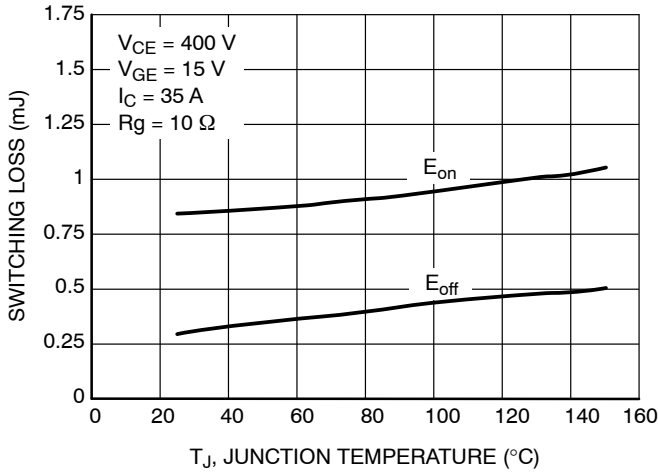


Figure 9. Switching Loss vs. Temperature

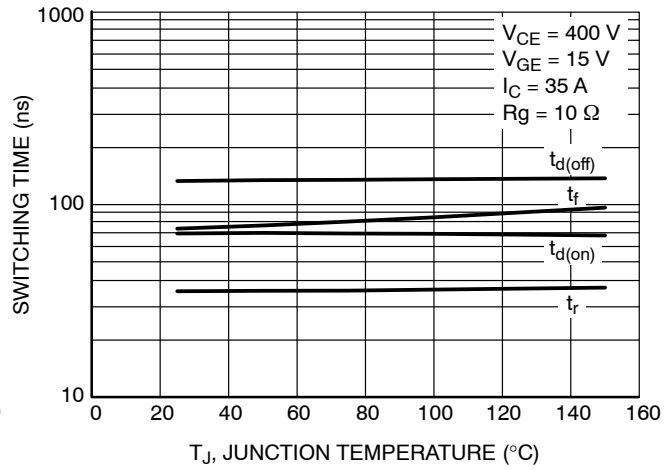


Figure 10. Switching Time vs. Temperature

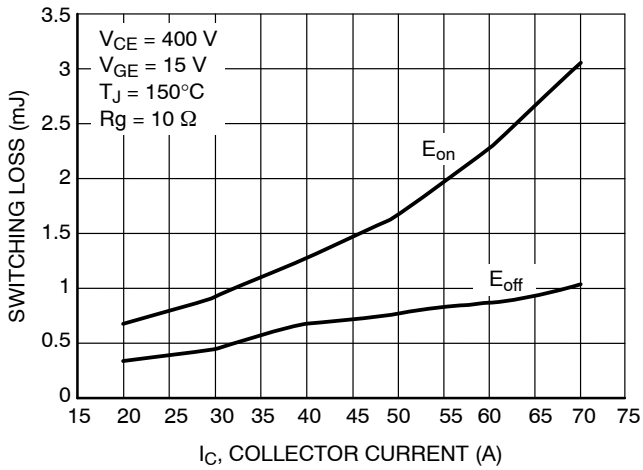


Figure 11. Switching Loss vs.  $I_C$

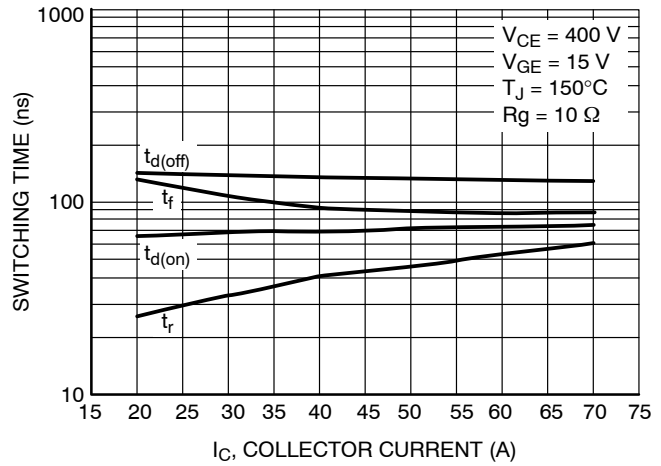


Figure 12. Switching Time vs.  $I_C$

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## TYPICAL CHARACTERISTICS

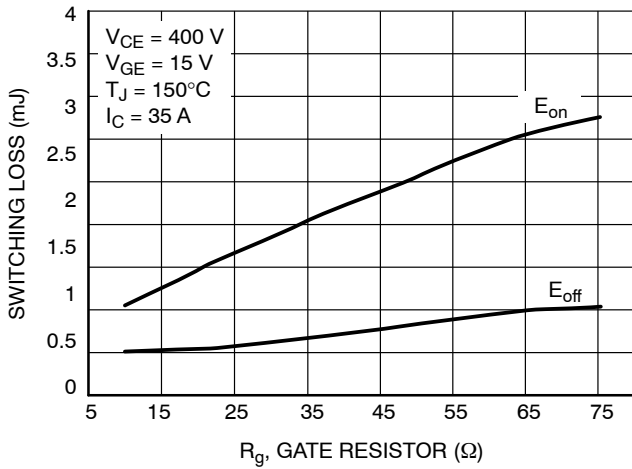


Figure 13. Switching Loss vs.  $R_g$

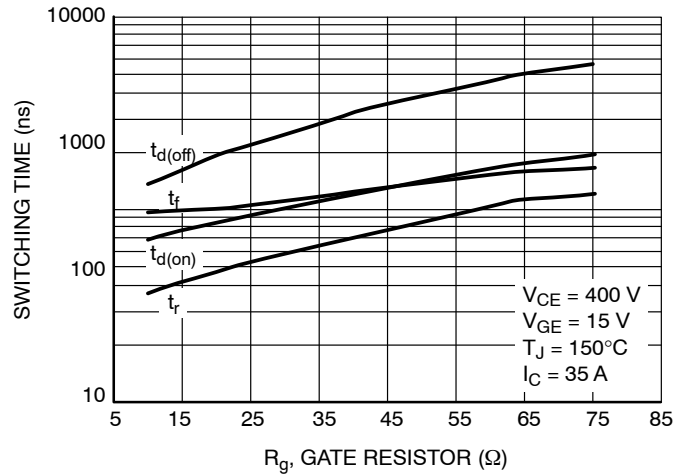


Figure 14. Switching Time vs.  $R_g$

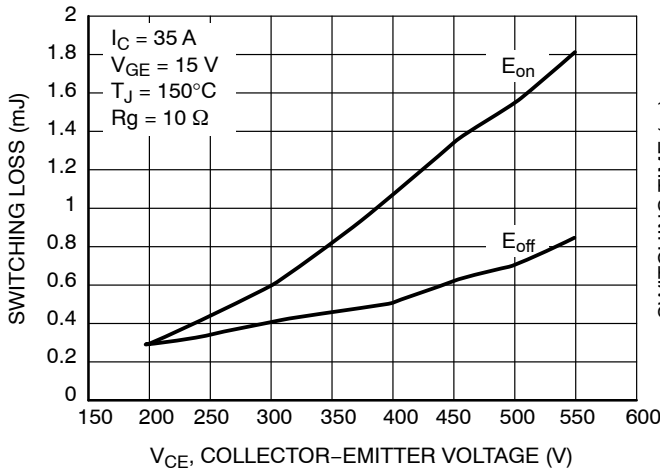


Figure 15. Switching Loss vs.  $V_{CE}$

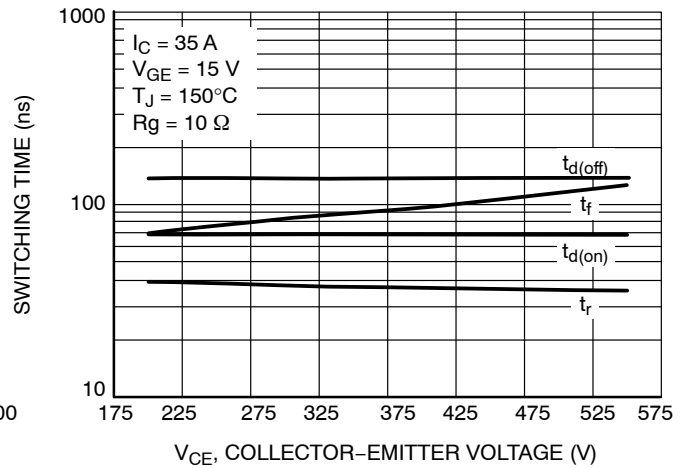


Figure 16. Switching Time vs.  $V_{CE}$

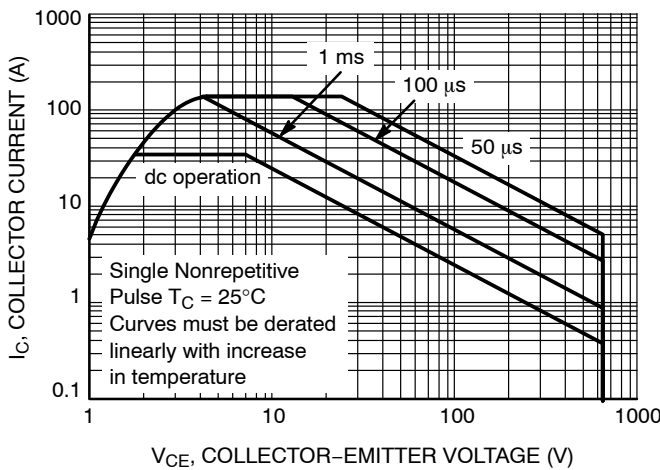


Figure 17. Safe Operating Area

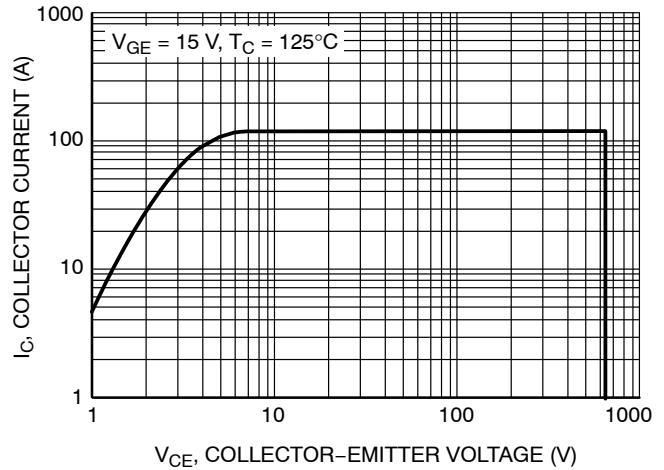
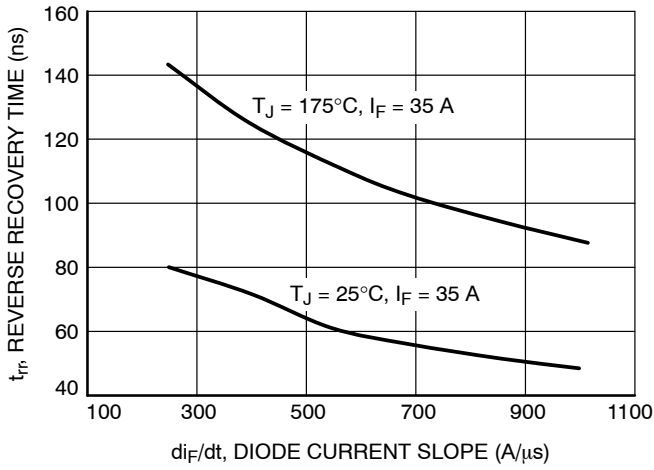


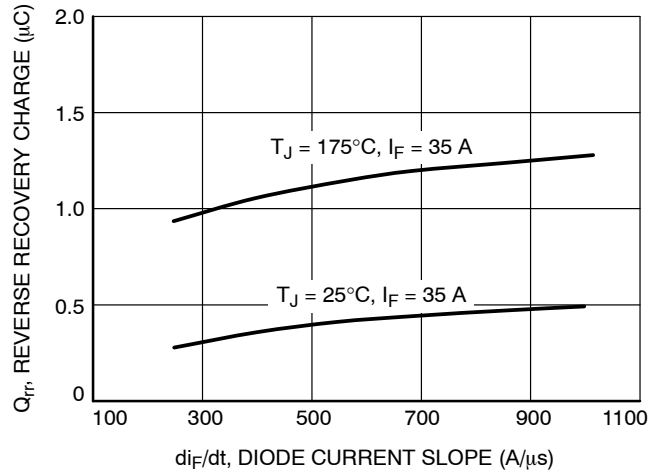
Figure 18. Reverse Bias Safe Operating Area

# NGTB35N65FL2WG

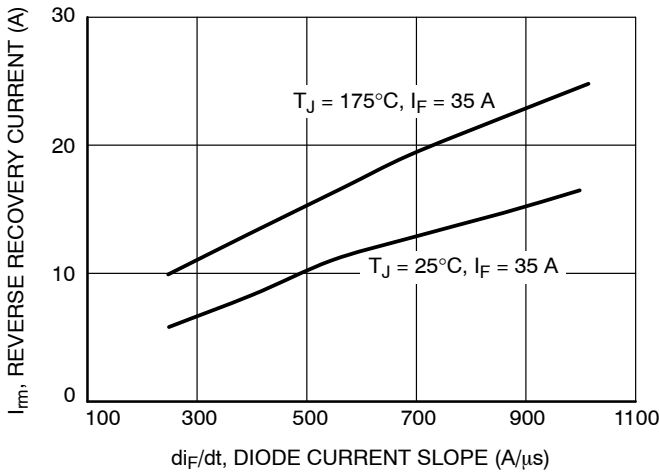
## TYPICAL CHARACTERISTICS



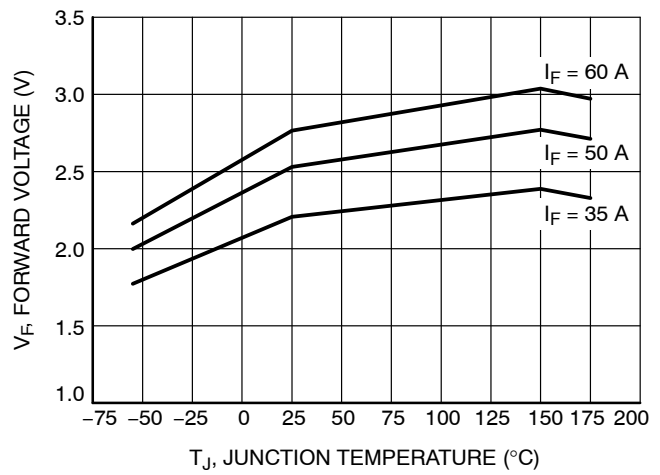
**Figure 19.  $t_{rr}$  vs.  $di_F/dt$   
( $V_R = 400$  V)**



**Figure 20.  $Q_{rr}$  vs.  $di_F/dt$   
( $V_R = 400$  V)**



**Figure 21.  $I_{rm}$  vs.  $di_F/dt$   
( $V_R = 400$  V)**



**Figure 22.  $V_F$  vs.  $T_J$**

# NGTB35N65FL2WG

## TYPICAL CHARACTERISTICS

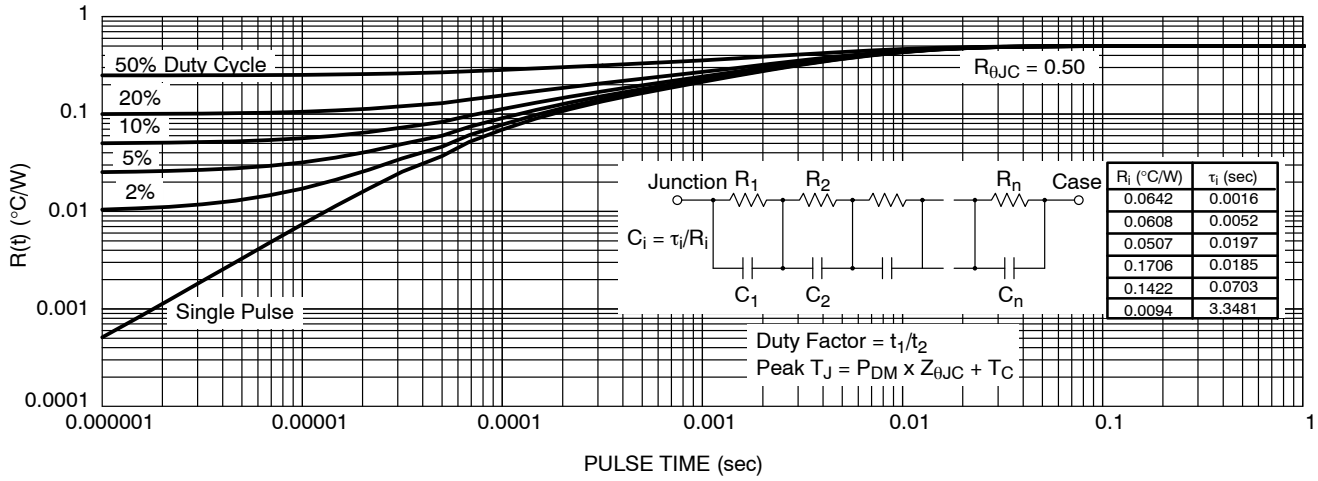


Figure 23. IGBT Transient Thermal Impedance

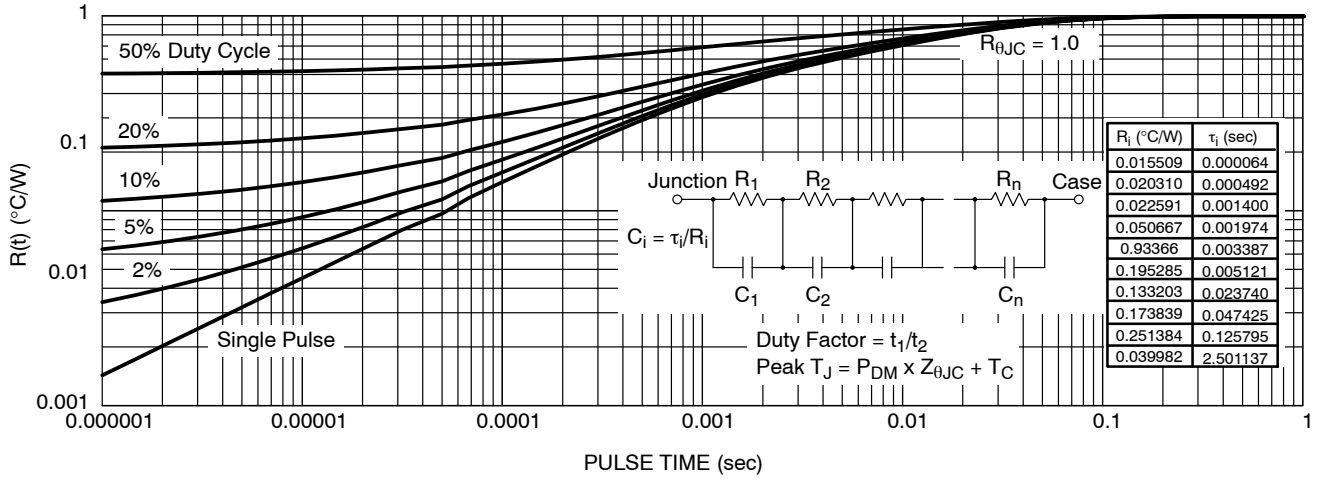
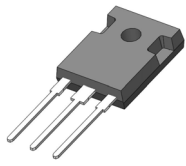


Figure 24. Diode Transient Thermal Impedance

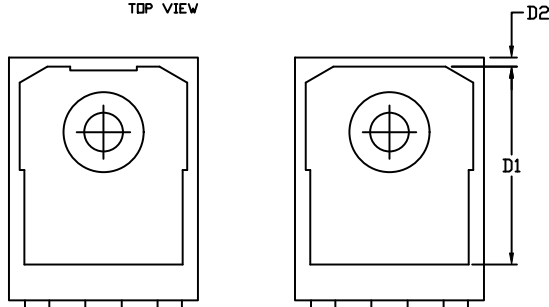
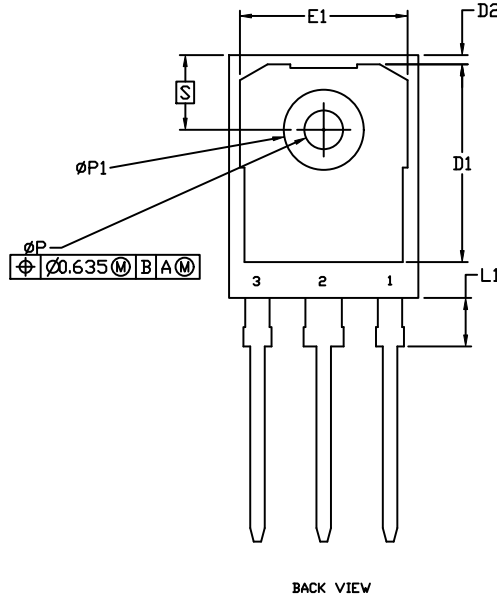
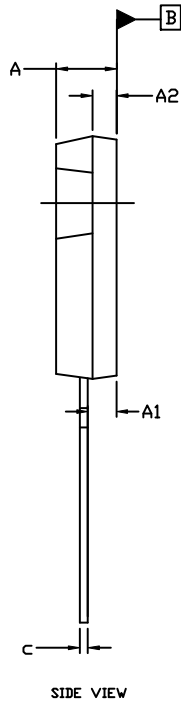
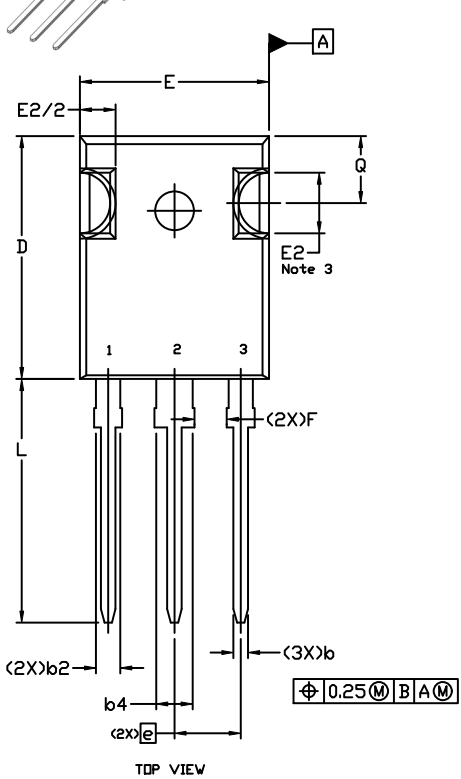
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



TO-247  
CASE 340AM  
ISSUE C

DATE 07 SEP 2021



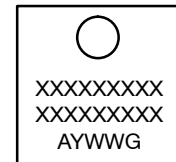
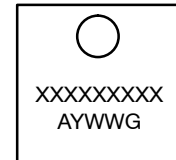
NOTE 4 HEATSINK SHAPES

NOTES:

1. DIMENSIONING AND TOLERANCE AS PER ASME Y14.5M, 2009.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. OPTIONAL BACK SIDE HEATSINK SHAPE.
5. DIMENSIONS ARE EXCLUSIVE OF BURRS AND MOLD FLASH. DIMENSIONS D AND E ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
6. DIMENSIONS A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
7. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.70	5.00	5.30
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b2	1.65	2.12	2.35
b4	2.60	3.12	3.40
c	0.45	0.60	0.75
D	20.80	21.00	21.34
D1	16.30	---	---
D2	0.75	---	---
E	15.50	16.00	16.25
E1	13.80	---	---
E2	4.32	4.90	5.49
e	5.45 BSC		
F	2.655	---	---
L	19.80	20.00	20.80
L1	3.81	4.20	4.35
P	3.55	3.60	3.65
P1	6.60	---	---
Q	5.40	6.00	6.20
S	6.15 BSC		

GENERIC MARKING DIAGRAMS\*



XXXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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